

RB521S30200 mA low V_F MEGA Schottky barrier rectifierRev. 01 - 6 October 2009

Product data sheet

1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD523 (SC-79) ultra small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Average forward current: I_{F(AV)} ≤ 0.2 A
- Reverse voltage: V_R ≤ 30 V
- Low reverse current: $I_R \le 30 \ \mu A$
- AEC-Q101 qualified
- Ultra small and flat lead SMD plastic package

1.3 Applications

- Low current rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1.Quick reference data

$T_j = 25 \circ C$ unless otherwise specified.

$I_{F(AV)} \\ Average forward current \\ Average forward current \\ \frac{\delta = 0.5;}{f = 20 \text{ kHz}} \\ \frac{T_{amb} \le 120 \text{ °C} [1]}{T_{sp} \le 140 \text{ °C}} \\ \frac{1}{T_{sp} \ge 140 $	1) = 20 00						
$ \begin{array}{c c} \delta = 0.5; \\ f = 20 \text{ kHz} \\ \hline T_{amb} \leq 120 \ ^\circ C & \fbox{11} \ - & - & 0.2 \ A \\ \hline T_{sp} \leq 140 \ ^\circ C & - & - & 0.2 \ A \\ \hline R & reverse current & V_R = 10 \ V & - & 2.5 \ 30 \ \mu A \\ \hline V_R & reverse voltage & - & - & 30 \ V \end{array} $	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\begin{tabular}{c c c c c c c c c c c c c c c c c c c $	I _{F(AV)}	average forward current	δ = 0.5;				
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$			$T_{amb} \le 120 \ ^{\circ}C$	<u>[1]</u>	-	0.2	А
V_R reverse voltage 30 V			$T_{sp} \le 140 \ ^{\circ}C$	-	-	0.2	А
	I _R	reverse current	V _R = 10 V	-	2.5	30	μA
	V _R	reverse voltage		-	-	30	V
V_F forward voltage $I_F = 0.2 \text{ A}$ \square - 420 500 m ³	V _F	forward voltage	I _F = 0.2 A	[2] _	420	500	mV

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, mounting pad for cathode 1 cm².



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2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outlin	e Graphic symbol
1	cathode	[1]	84
2	anode	1 2	1 🕂 2
			sym001

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering	g information		
Type number	Package		
	Name	Description	Version
RB521S30	SC-79	plastic surface-mounted package; 2 leads	SOD523

4. Marking

Table 4. Marking codes	
Type number	Marking code
RB521S30	ZB

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions			
-,		Conditions	Min	Max	Unit
V _R	reverse voltage	$T_j = 25 \ ^{\circ}C$	-	30	V
I _{F(AV)}	average forward current	square wave; $\delta = 0.5$; f = 20 kHz			
		$T_{amb} \le 120 \ ^{\circ}C$	<u>[1]</u> _	0.2	А
		$T_{sp} \le 140 \ ^{\circ}C$	-	0.2	А
I _{FSM}	non-repetitive peak forward current	t _p = 8.3 ms half sine wave; JEDEC method	[2] _	1	A
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[3][4]	275	mW
			[3][1]	420	mW
			[3][5]	500	mW

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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Т _ј	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[2] $T_i = 25 \,^{\circ}C$ prior to surge.

[3] Reflow soldering is the only recommended soldering method.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ui(ju)	thermal resistance from	in free air	<u>[1][2]</u>			
	junction to ambient		<u>[3]</u> _	-	455	K/W
			<u>[4]</u> _	-	300	K/W
			[5] _	-	250	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[6]</u> _	-	90	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

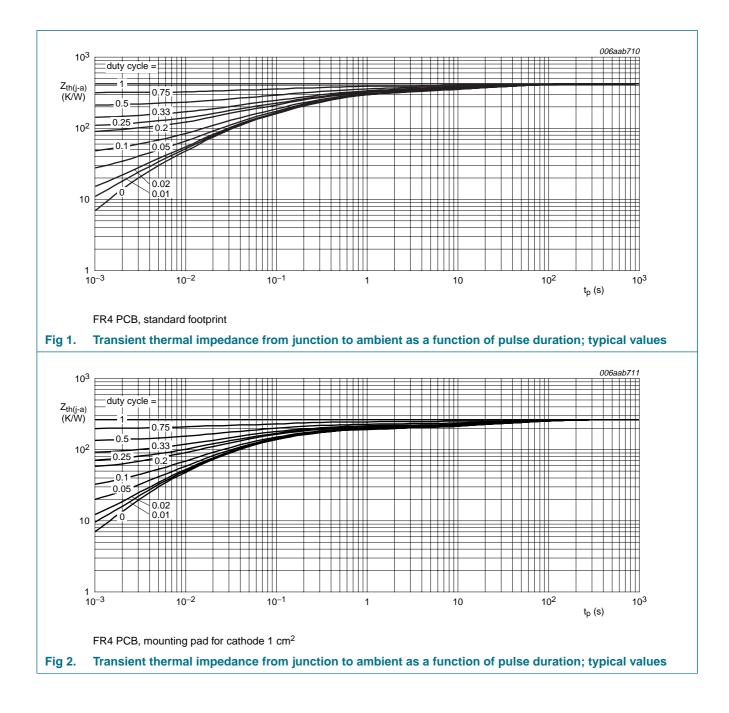
[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[5] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.

[6] Soldering point of cathode tab.

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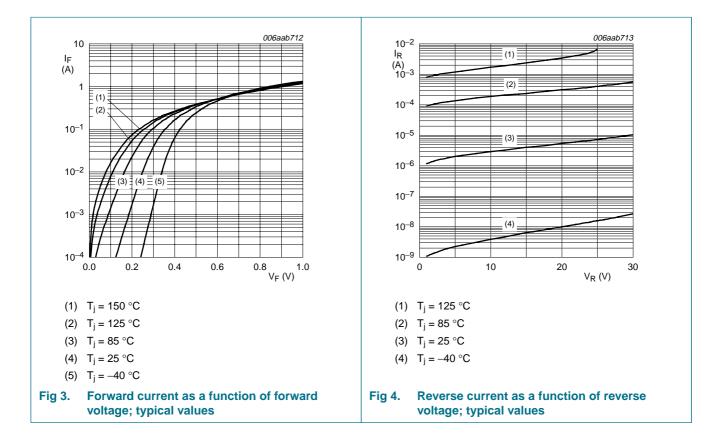


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7. Characteristics

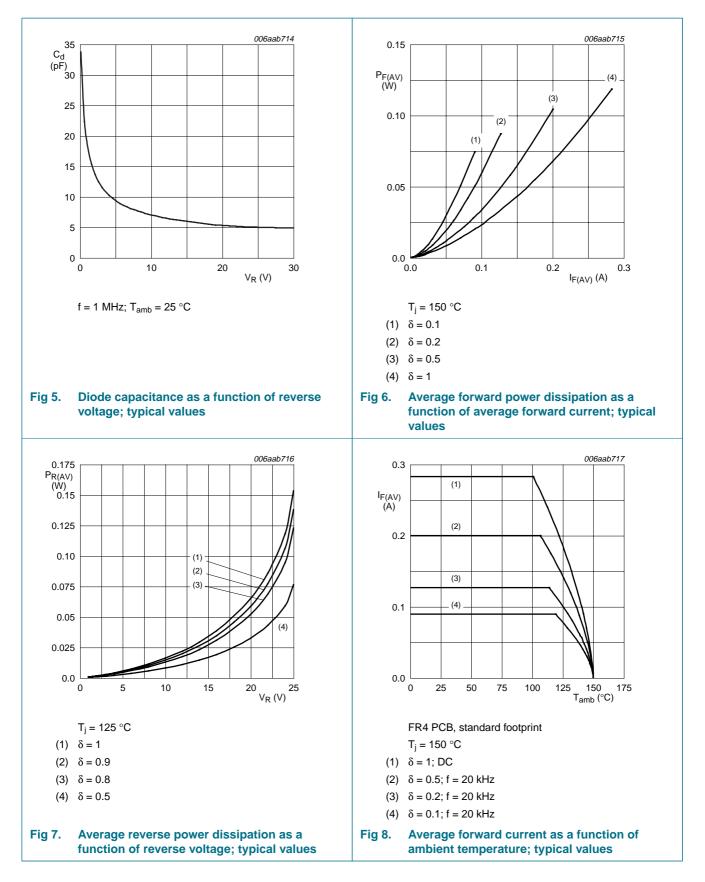
	Characteristics Inless otherwise specifie	ed.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F forward voltage			<u>[1]</u>			
		I _F = 0.1 mA	-	130	190	mV
		I _F = 1 mA	-	190	250	mV
		I _F = 10 mA	-	255	300	mV
		I _F = 100 mA	-	355	410	mV
		I _F = 200 mA	-	420	500	mV
I _R	reverse current	V _R = 10 V	-	2.5	30	μA
C _d	diode capacitance	$f = 1 \text{ MHz}; V_R = 1 \text{ V}$	-	20	25	pF



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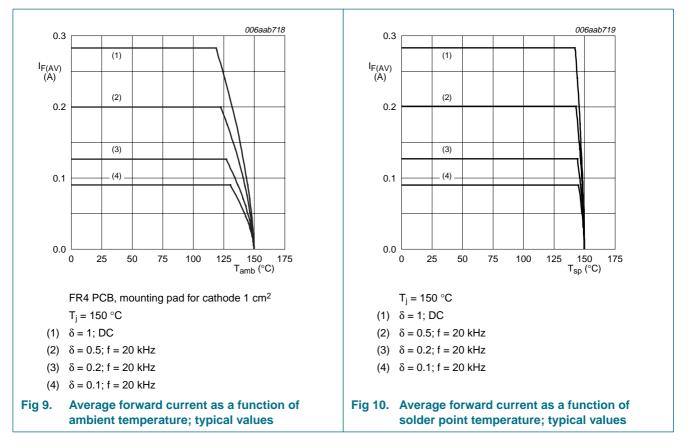
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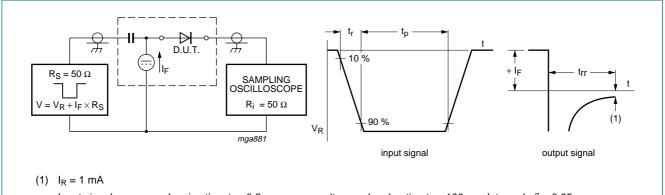


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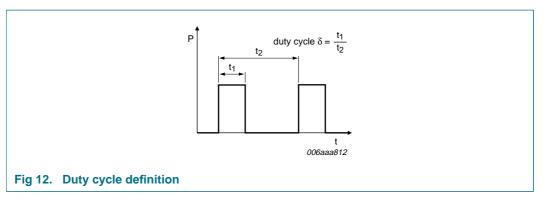
8. Test information



Input signal: reverse pulse rise time $t_r = 0.6$ ns; reverse voltage pulse duration $t_p = 100$ ns; duty cycle $\delta = 0.05$ Oscilloscope: rise time $t_r = 0.35$ ns

Fig 11. Reverse recovery time test circuit and waveforms

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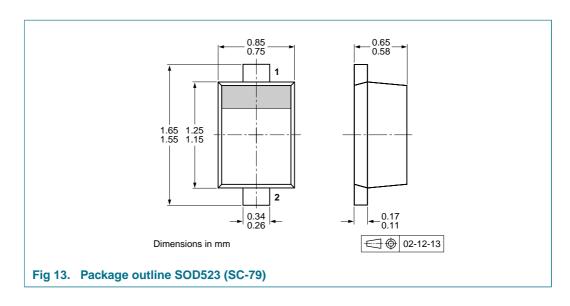
The current ratings for the typical waveforms as shown in Figure 8, 9 and 10 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current,

 $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



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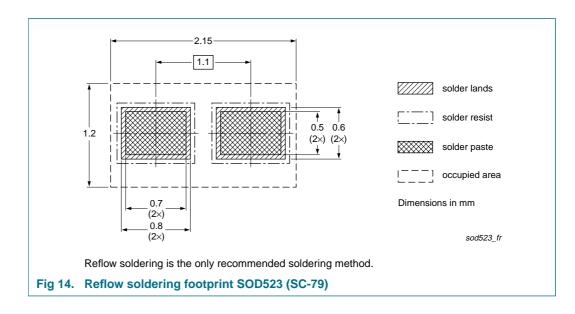
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10. Packing information

	king meth	ods last three digits of the 12NC ordering co	de.[<u>1]</u>		
Type number	Package	Description	Packin	ig quanti	ity
			3000	8000	10000
RB521S30	SOD523	2 mm pitch, 8 mm tape and reel	-	-315	-
		4 mm pitch, 8 mm tape and reel	-115	-	-135

[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



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12. Revision history

Table 9. R	evision history				
Document ID) Rel	lease date	Data sheet status	Change notice	Supersedes
RB521S30_1	200	091006 I	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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